

REMARKS

The Examiner indicated this application is in condition for allowance except for the following formal matters:

A. The title of the invention is not descriptive.

Applicants have amended the Title to "METHOD USING QUASI-PLANAR DOUBLE GATED FIN FIELD EFFECT TRANSISTOR PROCESS FOR THE FABRICATION OF A THYRISTOR-BASED STATIC READ/WRITE RANDOM-ACCESS MEMORY" to clearly indicate the invention to which the allowed method claims are directed.

B. Cancellation of non-elective device claims 11-20.

Applicants have canceled claims 11-20, but reserve the right to file a divisional patent application related thereto.

C. In Title, it is requested that Applicants spell out the acronym so as to avoid any possible confusion as to the meaning.

Applicants have replaced the acronym FINFET in the title with "Fin Field Effect Transistor". In addition, the acronym SRAM has been replaced with "Static Read/Write Random-Access Memory".

*Conclusion*

In view of the above, it is submitted that the claims are in condition for allowance. Allowance of claims 1-10 at an early date is solicited.

To the extent necessary, a petition for an extension of time under 37 C.F.R. 1.136 is hereby made. Please charge any shortage in fees due in connection with the filing of this paper, including any extension of time fees, to Deposit Account No. 50-0374 and please credit any excess fees to such deposit account.

Respectfully submitted,



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